



FSB50325T

Smart Power Module (SPM®)

Features

- 250V 3.0A 3-phase FRFET inverter including high voltage integrated circuit (HVIC)
- 3 divided negative dc-link terminals for inverter current sensing applications
- HVIC for gate driving and undervoltage protection
- 3/5V CMOS/TTL compatible, active-high interface
- Optimized for low electromagnetic interference
- Isolation voltage rating of 1500Vrms for 1min.
- Extended VB pin for PCB isolation

General Description

FSB50325T is a tiny smart power module (SPM®) based on FRFET technology as a compact inverter solution for small power motor drive applications such as fan motors and water suppliers. It is composed of 6 fast-recovery MOSFET (FRFET), and 3 half-bridge HVICs for FRFET gate driving. FSB50325T provides low electromagnetic interference (EMI) characteristics with optimized switching speed. Moreover, since it employs FRFET as a power switch, it has much better ruggedness and larger safe operation area (SOA) than that of an IGBT-based power module or one-chip solution. The package is optimized for the thermal performance and compactness for the use in the built-in motor application and any other application where the assembly space is concerned. FSB50325T is the most solution for the compact inverter providing the energy efficiency, compactness, and low electromagnetic interference.



Absolute Maximum Ratings

Symbol	Parameter	Conditions	Rating	Units
V_{PN}	DC Link Input Voltage, Drain-source Voltage of each FRFET		250	V
I_{D25}	Each FRFET Drain Current, Continuous	$T_C = 25^\circ\text{C}$	1.5	A
I_{D80}	Each FRFET Drain Current, Continuous	$T_C = 80^\circ\text{C}$	1.0	A
I_{DP}	Each FRFET Drain Current, Peak	$T_C = 25^\circ\text{C}$, $PW < 100\mu\text{s}$	3.0	A
P_D	Maximum Power Dissipation	$T_C = 25^\circ\text{C}$, Each FRFET	10	W
V_{CC}	Control Supply Voltage	Applied between V_{CC} and COM	20	V
V_{BS}	High-side Bias Voltage	Applied between $V_{B(U)}-U$, $V_{B(V)}-V$, $V_{B(W)}-W$	20	V
V_{IN}	Input Signal Voltage	Applied between IN and COM	-0.3 ~ $V_{CC}+0.3$	V
T_J	Operating Junction Temperature		-20 ~ 150	$^\circ\text{C}$
T_{STG}	Storage Temperature		-50 ~ 150	$^\circ\text{C}$
$R_{\theta JC}$	Junction to Case Thermal Resistance	Each FRFET under inverter operating condition (Note 1)	10.2	$^\circ\text{C}/\text{W}$
V_{ISO}	Isolation Voltage	60Hz, Sinusoidal, 1 minute, Connection pins to heatsink	1500	V_{rms}

Electrical Characteristics (T_J = 25°C, V_{CC}=V_{BS}=15V Unless Otherwise Specified)

Inverter Part (Each FRFET Unless Otherwise Specified)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{IN} = 0V, I _D = 250μA (Note 2)	250	-	-	V
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250μA, Referenced to 25°C	-	0.31	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{IN} = 0V, V _{DS} = 250V	-	-	250	μA
R _{DS(on)}	Static Drain-Source On-Resistance	V _{CC} = V _{BS} = 15V, V _{IN} = 5V, I _D = 1.0A	-	1.4	1.8	Ω
V _{SD}	Drain-Source Diode Forward Voltage	V _{CC} = V _{BS} = 15V, V _{IN} = 0V, I _D = -1.0A	-	-	1.2	V
t _{ON}	Switching Times	V _{PN} = 150V, V _{CC} = V _{BS} = 15V, I _D = 1.0A V _{IN} = 0V ↔ 5V Inductive load L=3mH High- and low-side FRFET switching (Note 3)	-	1076	-	ns
t _{OFF}			-	660	-	ns
t _{rr}			-	108	-	ns
E _{ON}			-	47	-	μJ
E _{OFF}			-	3.1	-	μJ
RBSOA	Reverse-bias Safe Operating Area	V _{PN} = 200V, V _{CC} = V _{BS} = 15V, I _D = I _{DP} , V _{DS} =BV _{DSS} , T _J = 150°C High- and low-side FRFET switching (Note 4)	Full Square			

Control Part (Each HVIC Unless Otherwise Specified)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
I _{QCC}	Quiescent V _{CC} Current	V _{CC} =15V, V _{IN} =0V Applied between V _{CC} and COM	-	-	160	μA
I _{QBS}	Quiescent V _{BS} Current	V _{BS} =15V, V _{IN} =0V Applied between V _{B(U)} -U, V _{B(V)} -V, V _{B(W)} -W	-	-	100	μA
UV _{CCD}	Low-side Undervoltage Protection (Figure 6)	V _{CC} Undervoltage Protection Detection Level	7.4	8.0	9.4	V
UV _{CCR}		V _{CC} Undervoltage Protection Reset Level	8.0	8.9	9.8	V
UV _{BSD}	High-side Undervoltage Protection (Figure 7)	V _{BS} Undervoltage Protection Detection Level	7.4	8.0	9.4	V
UV _{BSR}		V _{BS} Undervoltage Protection Reset Level	8.0	8.9	9.8	V
V _{IH}	ON Threshold Voltage	Logic High Level	2.9	-	-	V
V _{IL}	OFF Threshold Voltage	Logic Low Level				
I _{IH}	Input Bias Current	V _{IN} = 5V	-	10	20	μA
I _{IL}		V _{IN} = 0V	-	-	2	μA

Note:

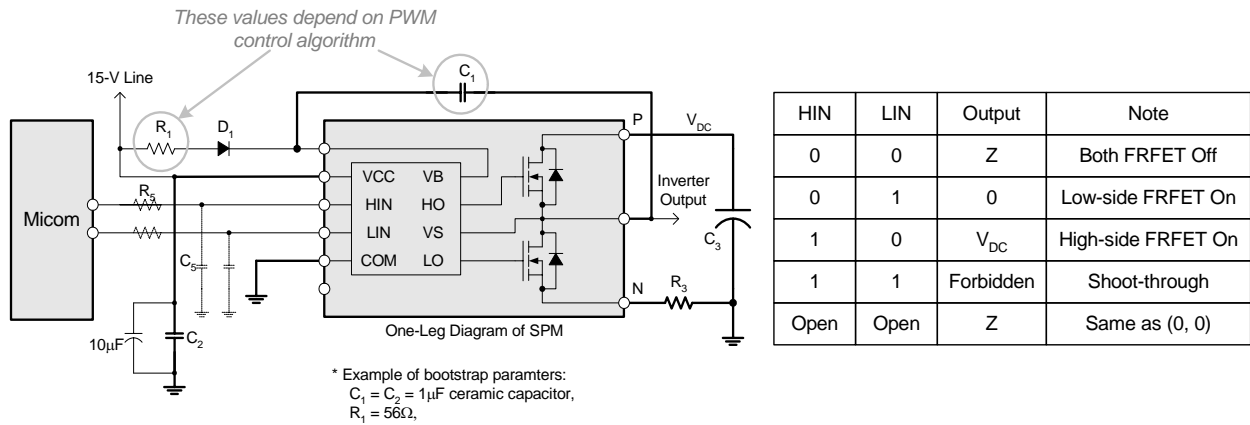
- For the measurement point of case temperature T_C, please refer to Figure 3 in page 4.
- BV_{DSS} is the absolute maximum voltage rating between drain and source terminal of each FRFET inside SPM®. V_{PN} should be sufficiently less than this value considering the effect of the stray inductance so that V_{DS} should not exceed BV_{DSS} in any case.
- t_{ON} and t_{OFF} include the propagation delay time of the internal drive IC. Listed values are measured at the laboratory test condition, and they can be different according to the field applications due to the effect of different printed circuit boards and wirings. Please see Figure 4 for the switching time definition with the switching test circuit of Figure 5.
- The peak current and voltage of each FRFET during the switching operation should be included in the safe operating area (SOA). Please see Figure 5 for the RBSOA test circuit that is same as the switching test circuit.

Package Marking & Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FSB50325T	FSB50325T	SPM23AC	-	-	15

Recommended Operating Conditions

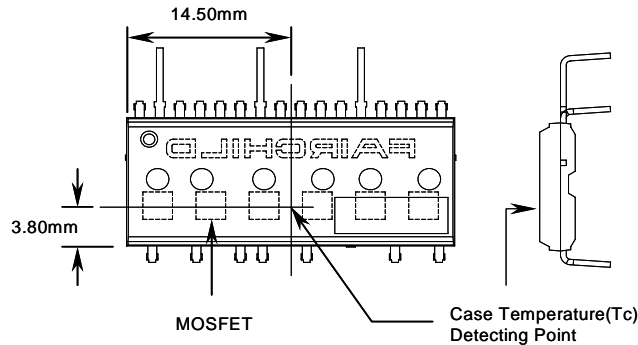
Symbol	Parameter	Conditions	Value			Units
			Min.	Typ.	Max.	
V_{PN}	Supply Voltage	Applied between P and N	-	150	200	V
V_{CC}	Control Supply Voltage	Applied between V_{CC} and COM	13.5	15	16.5	V
V_{BS}	High-side Bias Voltage	Applied between V_B and output(U, V, W)	13.5	15	16.5	V
$V_{IN(ON)}$	Input ON Threshold Voltage	Applied between IN and COM	3.0	-	V_{CC}	V
$V_{IN(OFF)}$	Input OFF Threshold Voltage		0	-	0.6	V
t_{dead}	Blanking Time for Preventing Arm-short	$V_{CC}=V_{BS}=13.5 \sim 16.5V, T_J \leq 150^\circ C$	1.0	-	-	μs
f_{PWM}	PWM Switching Frequency	$T_J \leq 150^\circ C$	-	15	-	kHz
T_C	Case Temperature	$T_J \leq 150^\circ C$	-20	-	125	$^\circ C$



Note:

- (1) It is recommended the bootstrap diode D_1 to have soft and fast recovery characteristics with 400-V rating
- (2) Parameters for bootstrap circuit elements are dependent on PWM algorithm. For 15 kHz of switching frequency, typical example of parameters is shown above.
- (3) RC coupling (R_5 and C_5) at each input (indicated as dotted lines) may be used to prevent improper input signal due to surge noise. Signal input of SPM® is compatible with standard CMOS or LSTTL outputs.
- (4) Bold lines should be short and thick in PCB pattern to have small stray inductance of circuit, which results in the reduction of surge voltage. Bypass capacitors such as C_1 , C_2 and C_3 should have good high-frequency characteristics to absorb high-frequency ripple current.

Figure 2. Recommended CPU Interface and Bootstrap Circuit with Parameters



Note:

Attach the thermocouple on top of the heatsink-side of SPM® (between SPM® and heatsink if applied) to get the correct temperature measurement.

Figure 3. Case Temperature Measurement

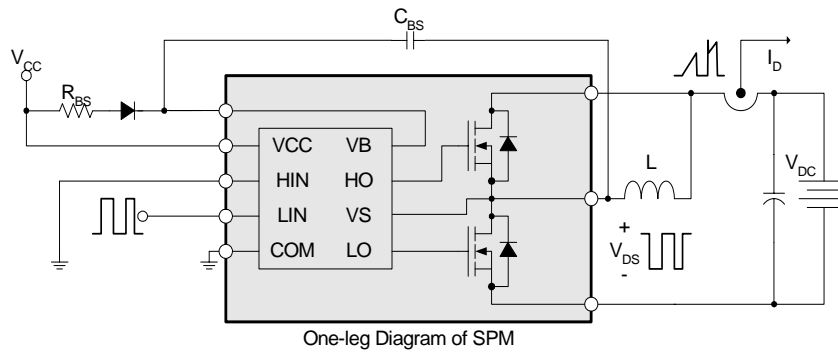
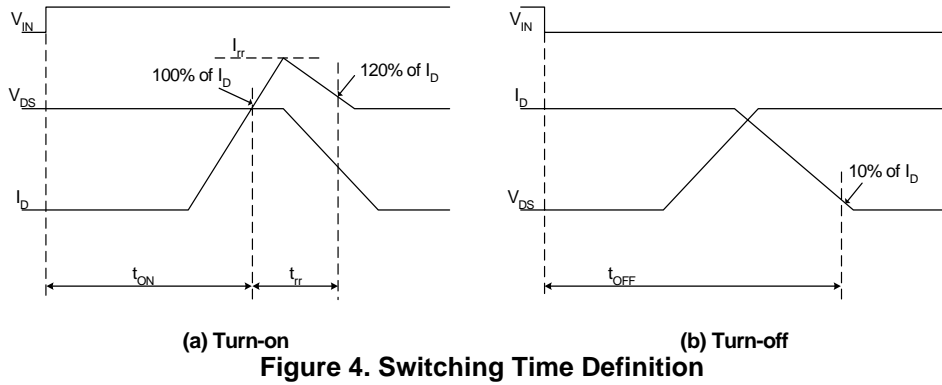


Figure 5. Switching and RBSOA(Single-pulse) Test Circuit (Low-side)

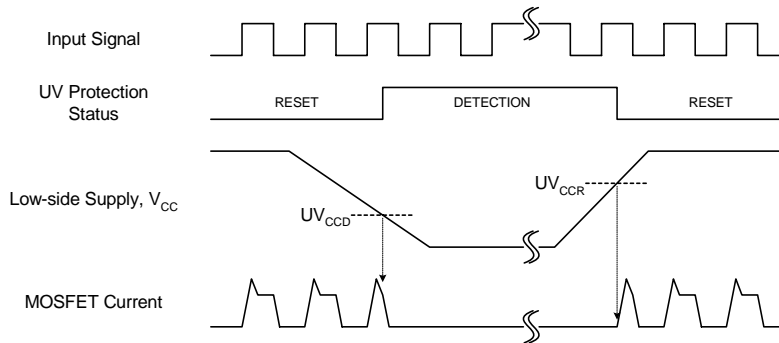


Figure 6. Undervoltage Protection (Low-side)

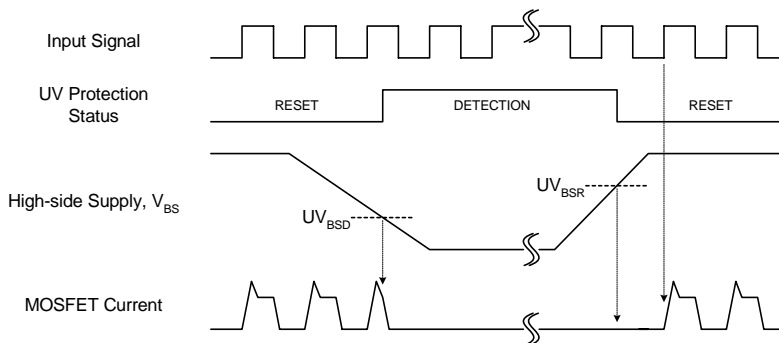
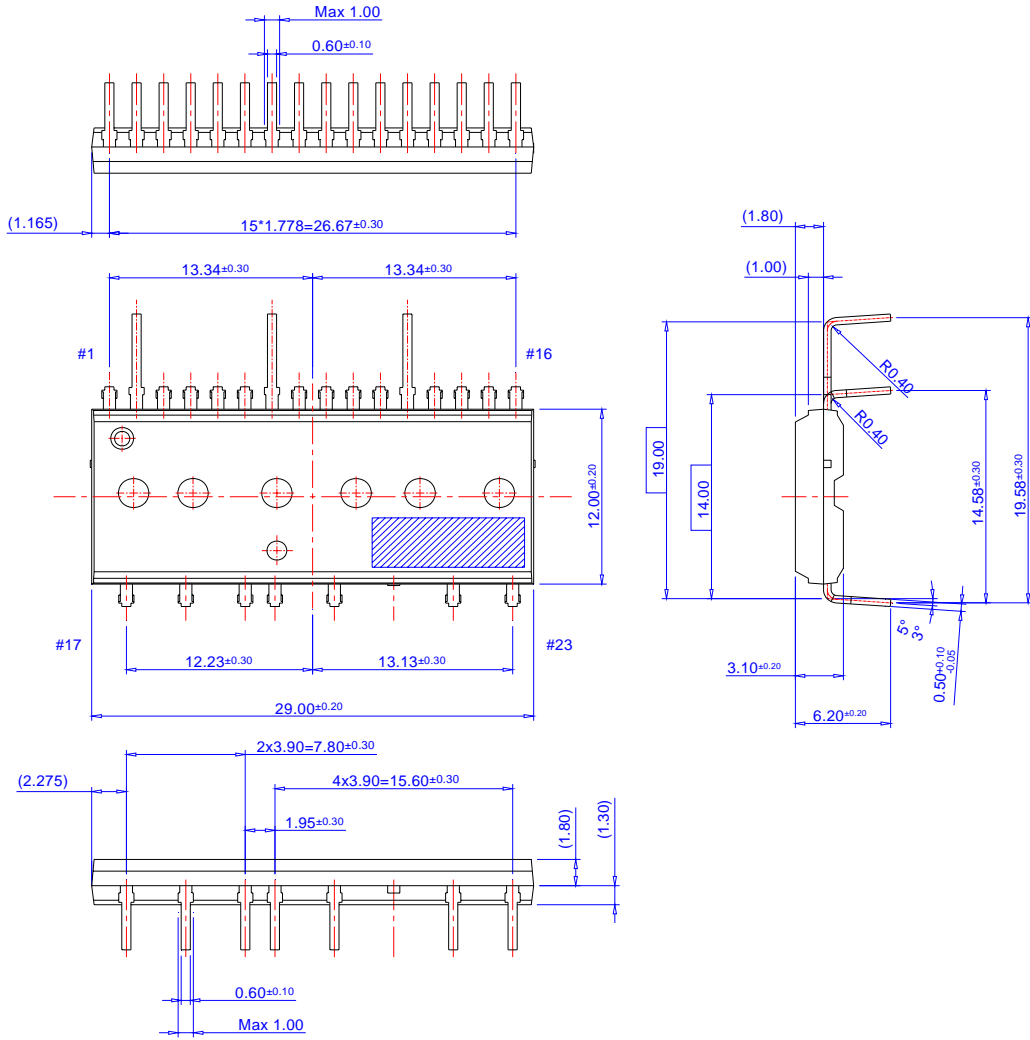


Figure 7. Undervoltage Protection (High-side)


Detailed Package Outline Drawings





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